GBU20005-GBU2010

Voltage 50V ~ 1000V

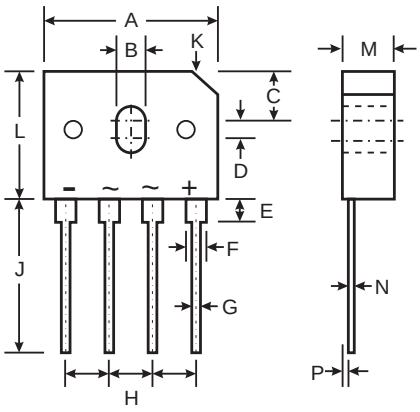
20Amp Glass Passivated Bridge Rectifiers

FEATURES

- I_o : 20A
- V_{RRM} : 50~1000V
- Glass passivated chip
- High surge forward current capability

APPLICATIONS

- General purpose 1 phase Bridge rectifier applications



GBU		
Dim	**Min**	**Max**
A	21.8	22.3
B	3.5	4.1
C	7.4	7.9
D	1.65	2.16
E	2.25	2.75
F	1.95	2.35
G	1.02	1.27
H	4.83	5.33
J	17.5	18.0
K	3.2 X 45°	
L	18.3	18.8
M	3.30	3.56
N	0.46	0.56
P	0.76	1.0
All Dimensions in mm		

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Rating 25°C ambient temperature unless otherwise specified. Single phase half wave, 60Hz, resistive or inductive load.
For capacitive load, de-rate current by 20%.)

Parameter		**Symbol**	**Part Number**							**Unit**
			GBU 20005	**GBU 2001**	**GBU 2002**	**GBU 2004**	**GBU 2006**	**GBU 2008**	**GBU 2010**	
Maximum Recurrent Peak Reverse Voltage		V_{RRM}	50	100	200	400	600	800	1000	V
Average Rectified Output Current @ 60Hz sine wave, R-load	With heatsink T_C =87℃	I_O	20							A
	Without heatsink T_A =25℃		3.5							
Surge (Nonrepetitive) Forward Current @ 60H_Z sine wave, 1 cycle, T_J=25℃		I_{FSM}	220							A
Current Squared Time [1]		I^2t	200							A^2S
Dielectric Strength@ Terminals to case，AC 1 minute		V_{DIS}	2.5							KV
Mounting Torque@ Recommend torque：5kg.cm		Tor	8							Kg.cm
Peak Forward Voltage@ I_{FM}=10A, Pulse measurement, Rating of per diode		V_{FM}	1.1							V
Peak Reverse Current@ V_{RM}=V_{RRM} , Pulse measurement, Rating of per diode		I_{RRM}	10							μA
Thermal Resistance	Without heatsink	$R_{\theta JA}$	22							℃ / W
	With heatsink	$R_{\theta JC}$	1.5							
Junction and Storage temperature range		T_J,T_{STG}	-55~+150							℃

Notes：

1. 1ms≤t<8.3ms T_J=25℃ ，Rating of per diode

RATINGS AND CHARACTERISTIC CURVES

FIG1:Io-Tc Curve

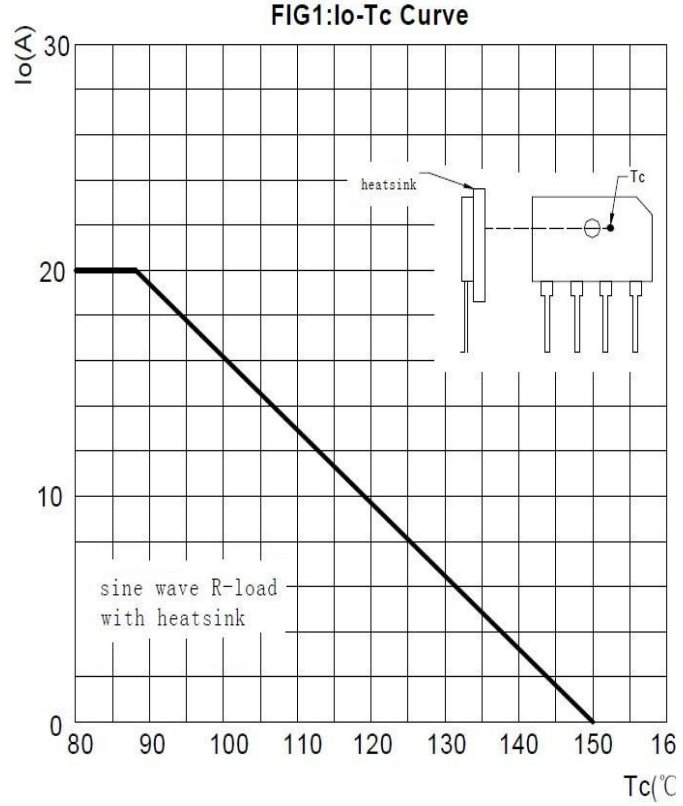


FIG2:Surge Forward Current Capadility

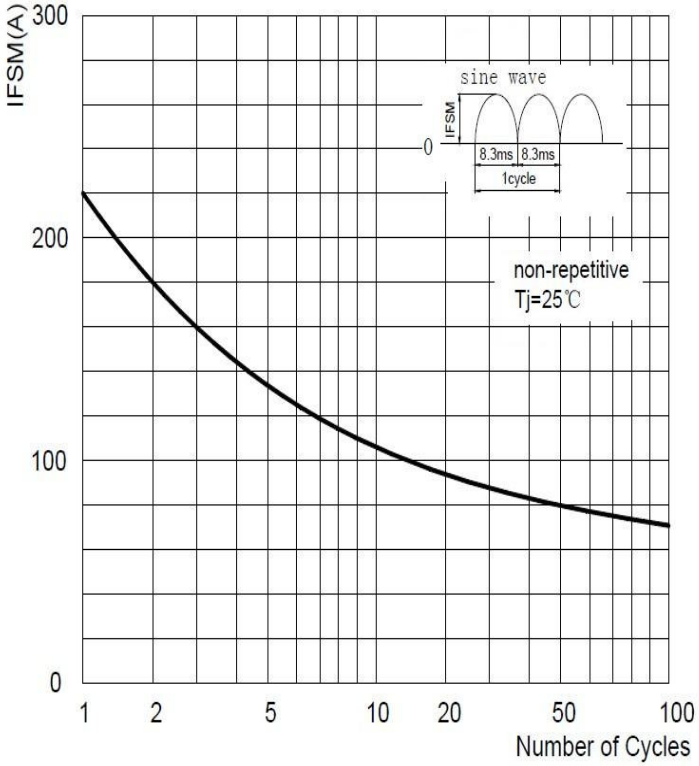


FIG3: Forward Voltage

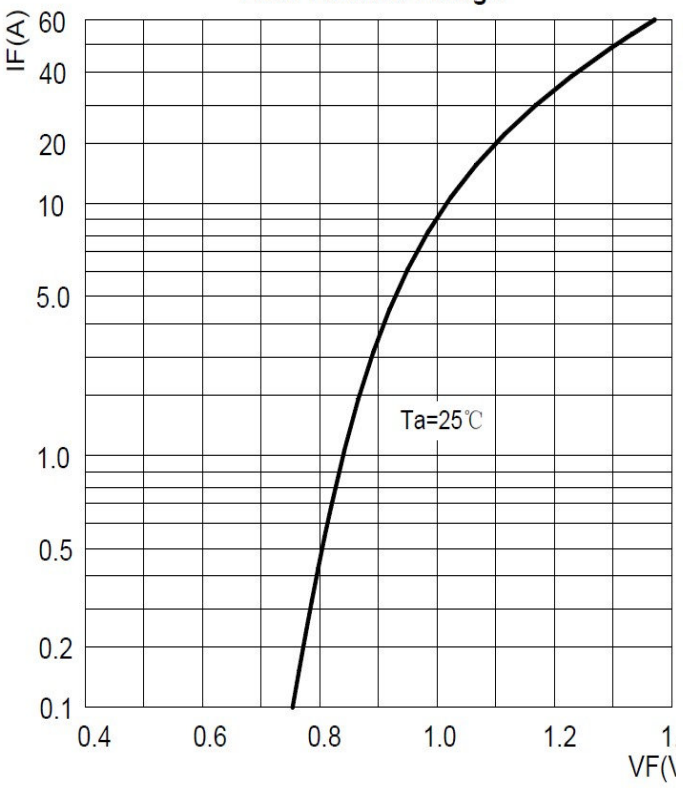


FIG4:Typical Reverse Characteristics